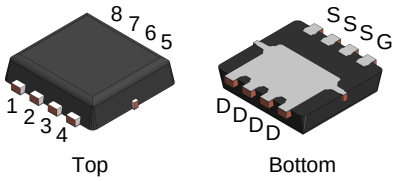
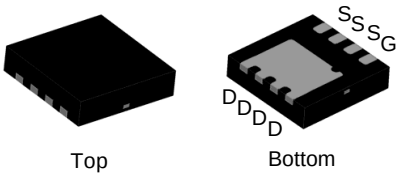
# MOSFET – N-Channel, Shielded Gate, POWERTRENCH®

## 150 V, 9.4 A, 134 mΩ

# FDMC86244, FDMC86244-L701




**WDFN8 3.3x3.3, 0.65P**
**CASE 511DR**
FDMC86244




**WDFN8 3.3x3.3, 0.65P**
**CASE 511DQ**
FDMC86244-L701

### General Description

This N-Channel MOSFET is produced using **onsemi**'s advanced POWERTRENCH process that incorporates Shielded Gate technology. This process has been optimized for the on-state resistance and yet maintain superior switching performance.

### Features

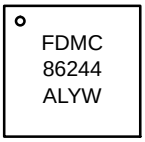
- Max $r_{DS(on)}$ = 134 mΩ at $V_{GS}$ = 10 V, $I_D$ = 2.8 A
- Max $r_{DS(on)}$ = 186 mΩ at $V_{GS}$ = 6 V, $I_D$ = 2.4 A
- Low Profile − 1 mm Max in Power 33
- 100% UIL Tested
- These Devices are Pb-Free and are RoHS Compliant

### Applications

- DC − DC Conversion

### MARKING DIAGRAM

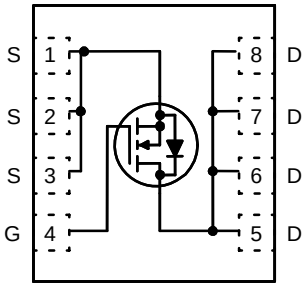
FDMC86244




FDMC86244-L701

| | |
|---|---|
| FDMC86244 | = Specific Device Code |
| A | = Assembly Site |
| XY | = 2-Digit Date Code |
| KK | = 2-Digit Lot Run Traceability Code |
| L | = Wafer Lot Number |
| YW | = Assembly Start Week |

### PIN ASSIGNMENT




### ORDERING INFORMATION

See detailed ordering and shipping information on page 6 of this data sheet.

NOTE: Some of the devices on this data sheet have been **DISCONTINUED**. Please refer to the table on page 6.

© Semiconductor Components Industries, LLC, 2012

**MOSFET MAXIMUM RATINGS** ($T_A$ = 25 °C unless otherwise noted)

| Symbol | Parameter | | | Ratings | Unit |
|---|---|---|---|---|---|
| $V_{DS}$ | Drain to Source Voltage | | | 150 | V |
| $V_{GS}$ | Gate to Source Voltage | | | ±20 | V |
| $I_D$ | Drain Current | Continuous | $T_C$ = 25 °C | 9.4 | A |
| | | Continuous (Note 2a) | $T_A$ = 25 °C | 2.8 | |
| | | Pulsed | | 12 | |
| $E_{AS}$ | Single Pulse Avalanche Energy (Note 1) | | | 12 | mJ |
| $P_D$ | Power Dissipation | | $T_C$ = 25 °C | 26 | W |
| | Power Dissipation (Note 2a) | | $T_A$ = 25 °C | 2.3 | |
| $T_J$, $T_{STG}$ | Operating and Storage Junction Temperature Range | | | −55 to +150 | °C |

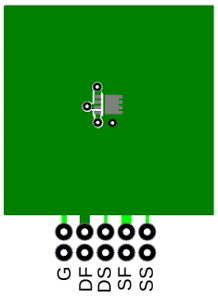
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Starting $T_J$ = 25 °C; N-ch: L = 1.0 mH, $I_{AS}$ = 5.0 A, $V_{DD}$ = 135 V, $V_{GS}$ = 10 V.

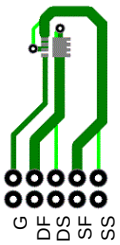
**THERMAL CHARACTERISTICS**

| Symbol | Parameter | Ratings | Unit |
|---|---|---|---|
| $R_{\theta JC}$ | Thermal Resistance, Junction to Case | 4.7 | °C/W |
| $R_{\theta JA}$ | Thermal Resistance, Junction to Ambient (Note 2a) | 125 | |

2. $R_{\theta JA}$ is determined with the device mounted on a 1 $in^2$ pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material. $R_{\theta JC}$ is guaranteed by design while $R_{\theta CA}$ is determined bythe user's board design.




a 53 °C/W when mounted on a 1 $in^2$ pad of 2 oz copper




b 125 °C/W when mounted on a minimum pad of 2 oz copper



Share Feedback
Your Opinion Matters

**ELECTRICAL CHARACTERISTICS** ($T_J$ = 25 °C unless otherwise noted)

| Symbol | Parameter | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| **OFF CHARACTERISTICS** | | | | | | |
| $BV_{DSS}$ | Drain to Source Breakdown Voltage | $I_D$ = 250 μA, $V_{GS}$ = 0 V | 150 | – | – | V |
| $\Delta BV_{DSS}$ / $\Delta T_J$ | Breakdown Voltage Temperature Coefficient | $I_D$ = 250 μA, referenced to 25 °C | – | 106 | – | mV/°C |
| $I_{DSS}$ | Zero Gate Voltage Drain Current | $V_{DS}$ = 120 V, $V_{GS}$ = 0 V | – | – | 1 | μA |
| $I_{GSS}$ | Gate to Source Leakage Current | $V_{GS}$ = ±20 V, $V_{DS}$ = 0 V | – | – | ±100 | nA |
| **ON CHARACTERISTICS** | | | | | | |
| $V_{GS(th)}$ | Gate to Source Threshold Voltage | $V_{GS}$ = $V_{DS}$, $I_D$ = 250 μA | 2 | 2.6 | 4 | V |
| $\Delta V_{GS(th)}$ / $\Delta T_J$ | Gate to Source Threshold Voltage Temperature Coefficient | $I_D$ = 250 μA, referenced to 25 °C | – | −9 | – | mV/°C |
| $r_{DS(on)}$ | Static Drain to Source On Resistance | $V_{GS}$ = 10 V, $I_D$ = 2.8 A | – | 105 | 134 | mΩ |
| | | $V_{GS}$ = 6 V, $I_D$ = 2.4 A | – | 120 | 186 | |
| | | $V_{GS}$ = 10 V, $I_D$ = 2.8 A, $T_J$ = 125 °C | – | 199 | 254 | |
| $g_{FS}$ | Forward Transconductance | $V_{DS}$ = 10 V, $I_D$ = 2.8 A | – | 8 | – | S |
| **DYNAMIC CHARACTERISTICS** | | | | | | |
| $C_{iss}$ | Input Capacitance | $V_{DS}$ = 75 V, $V_{GS}$ = 0 V, f = 1 MHz | – | 257 | 345 | pF |
| $C_{oss}$ | Output Capacitance | | – | 32 | 45 | pF |
| $C_{rss}$ | Reverse Transfer Capacitance | | – | 1.8 | 5 | pF |
| **SWITCHING CHARACTERISTICS** | | | | | | |
| $t_{d(on)}$ | Turn-On Delay Time | $V_{DD}$ = 75 V, $I_D$ = 2.8 A, $V_{GS}$ = 10 V, $R_{GEN}$ = 6 Ω | – | 5.3 | 11 | ns |
| $t_r$ | Rise Time | | – | 1.5 | 10 | ns |
| $t_{d(off)}$ | Turn-Off Delay Time | | – | 9.9 | 20 | ns |
| $t_f$ | Fall Time | | – | 2.3 | 10 | ns |
| $Q_{g(TOT)}$ | Total Gate Charge | $V_{GS}$ = 0 V to 10 V, $V_{DD}$ = 75 V, $I_D$ = 2.8 A | – | 4.2 | 5.9 | nC |
| $Q_{g(TOT)}$ | Total Gate Charge | $V_{GS}$ = 0 V to 5 V, $V_{DD}$ = 75 V, $I_D$ = 2.8 A | – | 2.4 | 3.4 | nC |
| $Q_{gs}$ | Total Gate Charge | $V_{DD}$ = 75 V, $I_D$ = 2.8 A | – | 1.1 | – | nC |
| $Q_{gd}$ | Gate to Drain “Miller” Charge | | – | 1.0 | – | nC |
| **DRAIN-SOURCE DIODE CHARACTERISTICS** | | | | | | |
| $V_{SD}$ | Source to Drain Diode Forward Voltage | $V_{GS}$ = 0 V, $I_S$ = 2.8 A (Note 3) | – | 0.81 | 1.3 | V |
| | | $V_{GS}$ = 0 V, $I_S$ = 2 A (Note 3) | – | 0.79 | 1.2 | |
| $t_{rr}$ | Reverse Recovery Time | $I_F$ = 2.8 A, di/dt = 100 A/μs | – | 48 | 76 | ns |
| $Q_{rr}$ | Reverse Recovery Charge | | – | 38 | 61 | nC |

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

3. Pulse Test: Pulse Width < 300 μs, Duty cycle < 2.0%.



Share Feedback
Your Opinion Matters

## TYPICAL CHARACTERISTICS ($T_J$ = 25 °C unless otherwise noted)

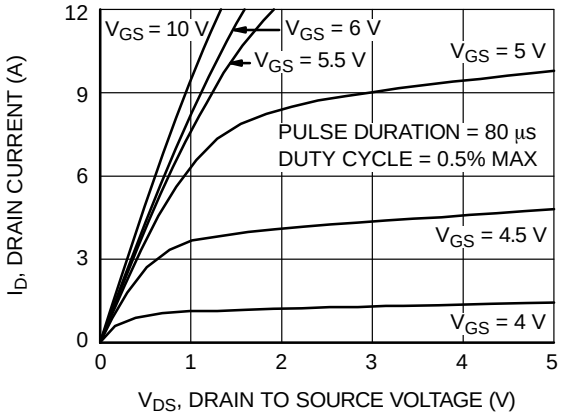



**Figure 1. On Region Characteristics**

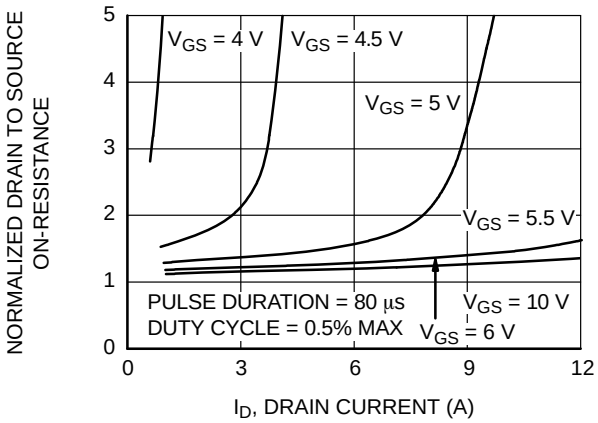



**Figure 2. Normalized On-Resistance vs. Drain Current and Gate Voltage**

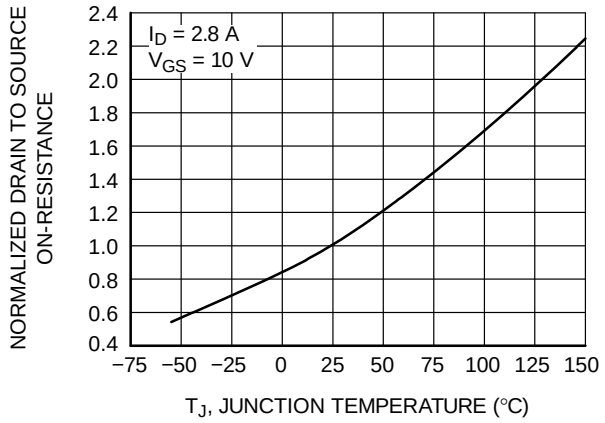



**Figure 3. Normalized On Resistance vs. Junction Temperature**

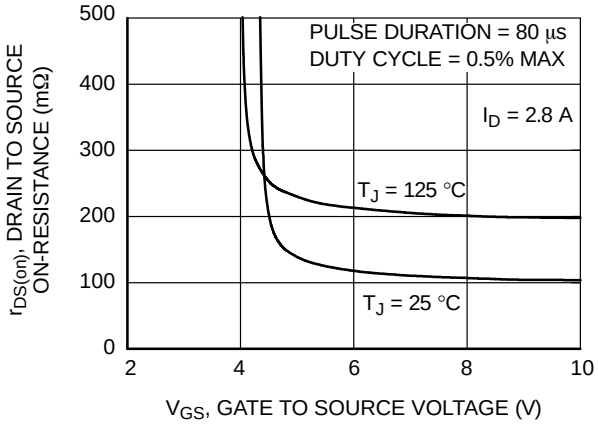



**Figure 4. On-Resistance vs. Gate to Source Voltage**

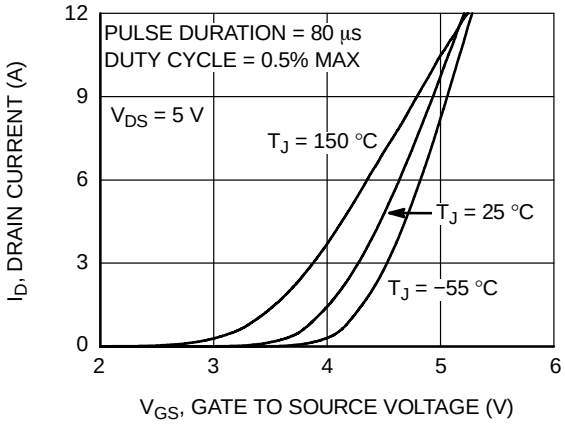



**Figure 5. Transfer Characteristics**

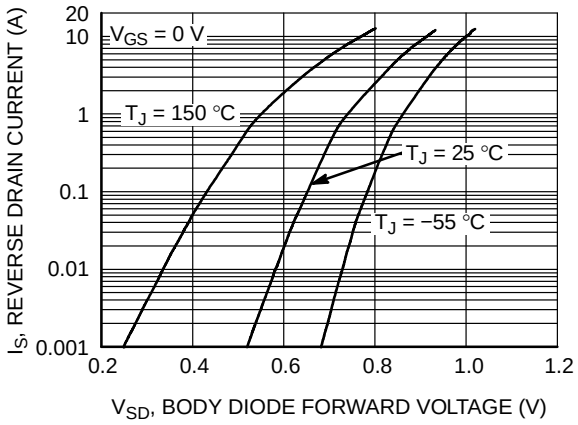



**Figure 6. Source to Drain Diode Forward Voltage vs. Source Current**



Share Feedback
Your Opinion Matters

## TYPICAL CHARACTERISTICS ($T_J$ = 25 °C unless otherwise noted) (continued)

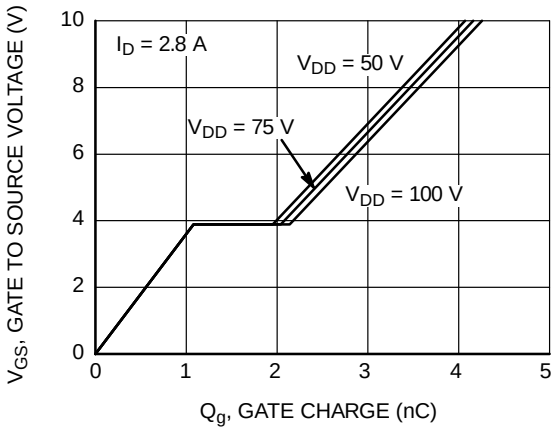



**Figure 7. Gate Charge Characteristics**

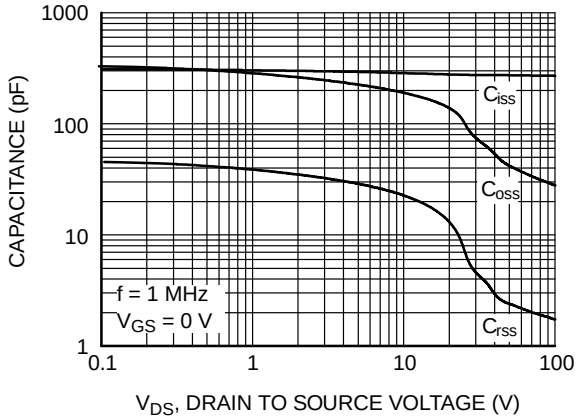



**Figure 8. Capacitance vs. Drain to Source Voltage**

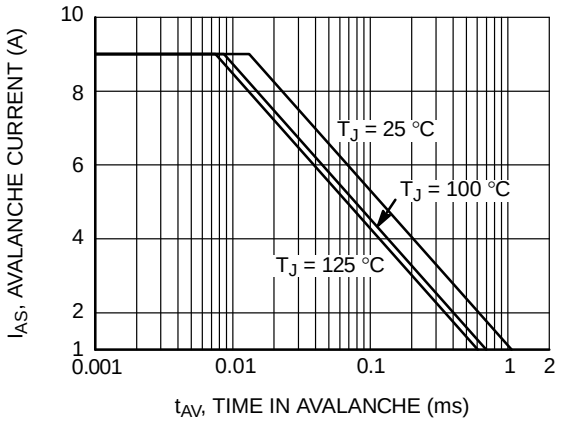



**Figure 9. Unclamped Inductive Switching Capability**

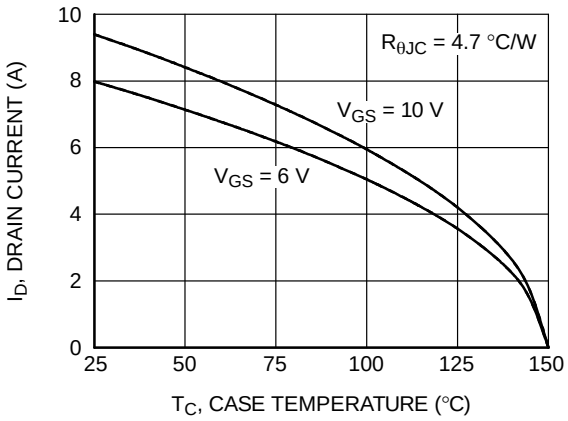



**Figure 10. Maximum Continuous Drain Current vs. Case Temperature**

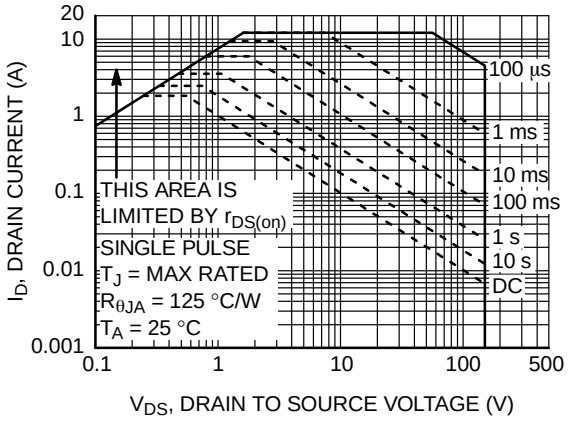



**Figure 11. Forward Bias Safe Operating Area**

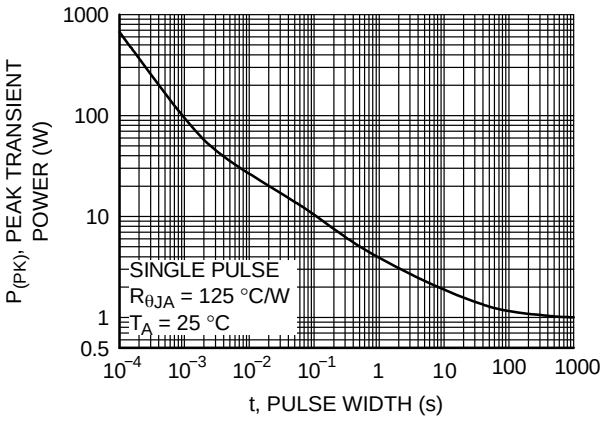



**Figure 12. Single Pulse Maximum Power Dissipation**



Share Feedback
Your Opinion Matters

## TYPICAL CHARACTERISTICS ($T_J$ = 25 °C unless otherwise noted) (continued)

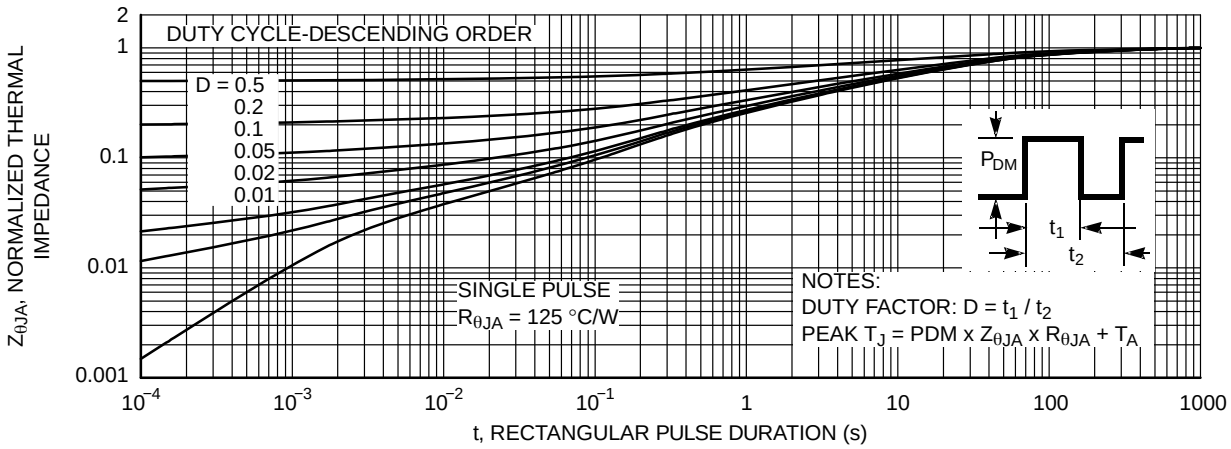



**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**

### ORDERING INFORMATION

| Device | Device Marking | Package Type | Reel Size | Tape Width | Shipping† |
|---|---|---|---|---|---|
| FDMC86244 | FDMC86244 | WDFN8 3.3x3.3, 0.65P Power 33 (Pb-Free) | 13” | 12 mm | 3000 / Tape & Reel |

**DISCONTINUED** (Note 4)

| | | | | | |
|---|---|---|---|---|---|
| FDMC86244-L701 | FDMC86244 | WDFN8 3.3x3.3, 0.65P Power 33 (Pb-Free) | 13” | 12 mm | 3000 / Tape & Reel |

† For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

4. **DISCONTINUED:** This device is not available. Please contact your **onsemi** representative for information. The most current information on this device may be available on www.onsemi.com.

POWERTRENCH is registered trademark of Semiconductor Components Industries, LLC dba “**onsemi**” or its affiliates and/or subsidiaries in the United States and/or other countries.



Share Feedback
Your Opinion Matters

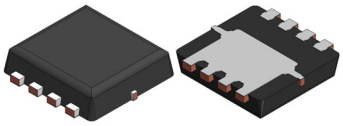
## REVISION HISTORY

| Revision | Description of Changes | Date |
|---|---|---|
| 4 | Rebranded the document to **onsemi** format. FDMC86244-L701 OPN marked as Discontinued. | 2/16/2026 |

This document has undergone updates prior to the inclusion of this revision history table. The changes tracked here only reflect updates made on the noted approval dates.

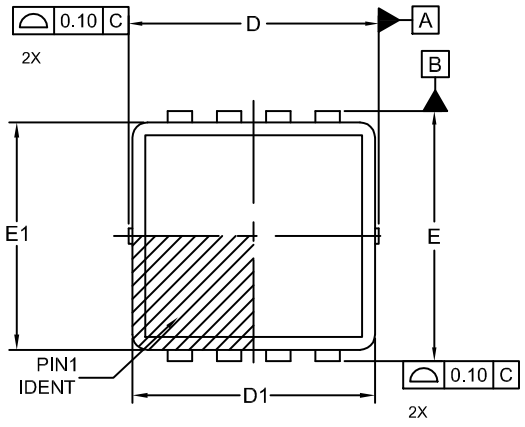


Share Feedback
Your Opinion Matters

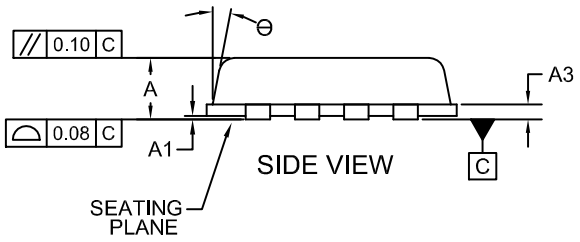


**WDFN8 3.3x3.3, 0.65P**
CASE 511DR
ISSUE B

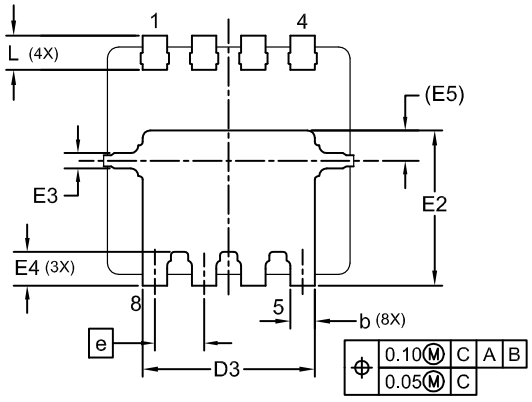
DATE 02 FEB 2022




TOP VIEW



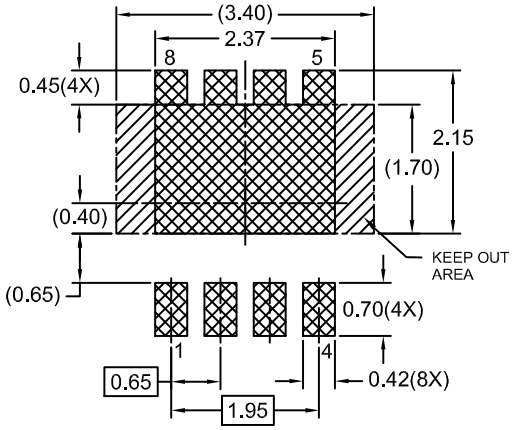

SIDE VIEW




BOTTOM VIEW

NOTES:
A. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
B. SEATING PLANE IS DEFINED BY TERMINAL TIPS ONLY
C. BODY DIMENSIONS DO NOT INCLUDE MOLD FLASH PROTRUSIONS NOR GATE BURRS. MOLD FLASH PROTRUSION OR GATE BURR DOES NOT EXCEED 0.150MM.

| DIM | MILLIMETERS | | |
|---|---|---|---|
| | MIN | NOM | MAX |
| A | 0.70 | 0.75 | 0.80 |
| A1 | 0.00 | - | 0.05 |
| A3 | 0.15 | 0.20 | 0.25 |
| b | 0.27 | 0.32 | 0.37 |
| D | 3.20 | 3.30 | 3.40 |
| D1 | 3.10 | 3.20 | 3.30 |
| D3 | 2.17 | 2.27 | 2.37 |
| E | 3.20 | 3.30 | 3.40 |
| E1 | 2.90 | 3.00 | 3.10 |
| E2 | 1.95 | 2.05 | 2.15 |
| E3 | 0.15 | 0.20 | 0.25 |
| E4 | 0.30 | 0.40 | 0.50 |
| E5 | 0.40 REF | | |
| e | 0.65 BSC | | |
| L | 0.30 | 0.40 | 0.50 |
| θ | 0° | - | 12° |




RECOMMENDED LAND PATTERN

*FOR ADDITIONAL INFORMATION ON OUR PB-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES REFERENCE MANUAL, SOLDERRM/D.

**GENERIC MARKING DIAGRAM***

XXXX = Specific Device Code
A = Assembly Location
Y = Year
WW = Work Week
▪ = Pb−Free Package

(Note: Microdot may be in either location)

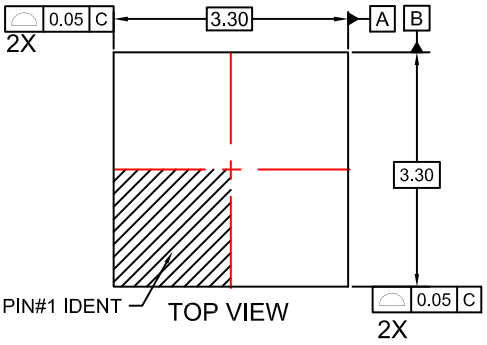
*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, “G” or microdot “▪”, may or may not be present. Some products may not follow the Generic Marking.

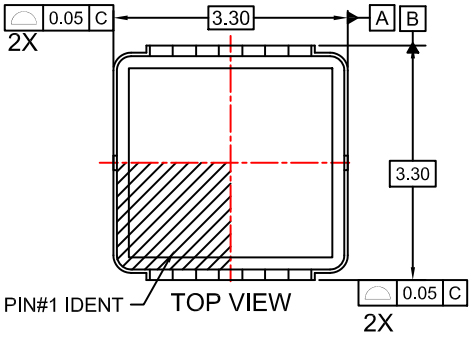
| | | |
|---|---|---|
| **DOCUMENT NUMBER:** | **98AON13650G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped “CONTROLLED COPY” in red. |
| **DESCRIPTION:** | **WDFN8 3.3x3.3, 0.65P** | **PAGE 1 OF 1** |

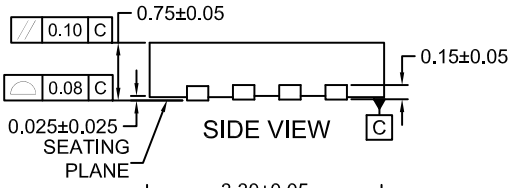
**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

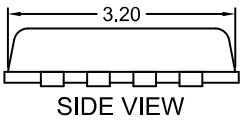
**WDFN8 3.3x3.3, 0.65P**
CASE 511DQ
ISSUE O

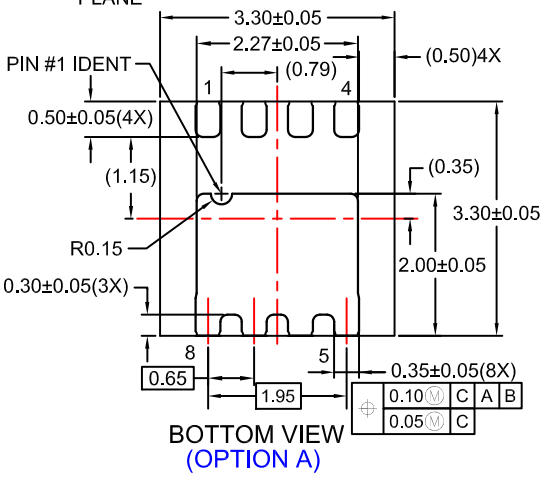
DATE 31 OCT 2016

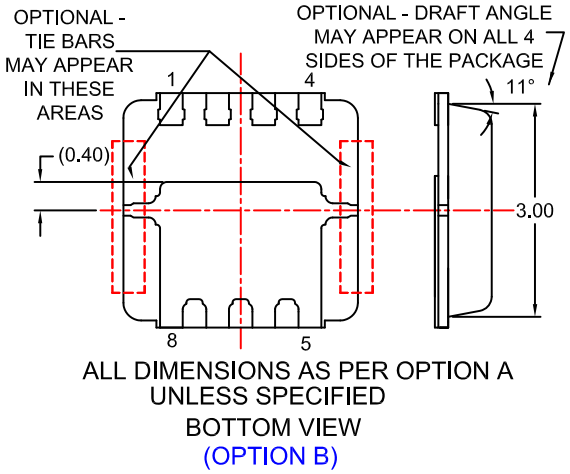


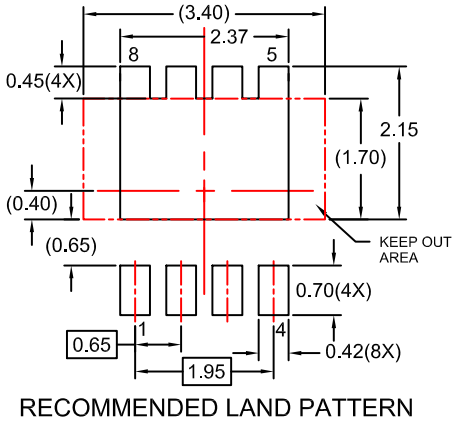



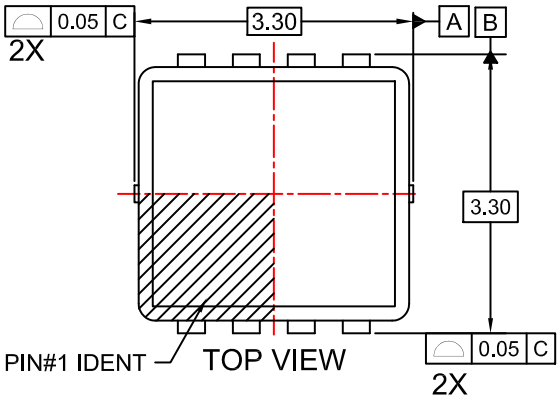



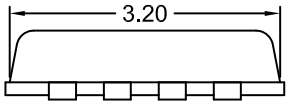

| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON13648G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
| **DESCRIPTION:** | **WDFN8 3.3X3.3, 0.65P** | | **PAGE 1 OF 2** |

**onsemi** and onsemi are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

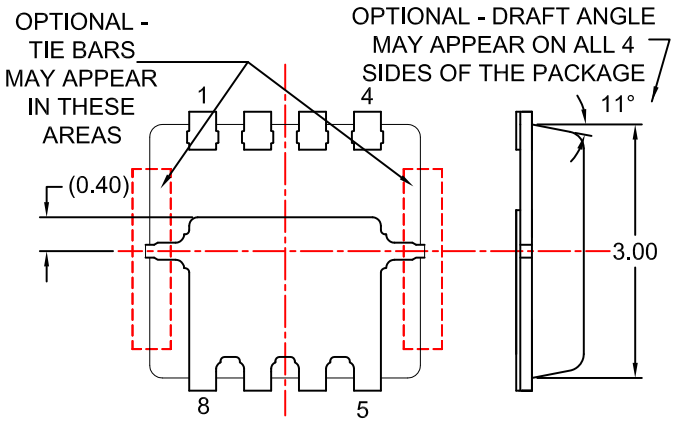
**WDFN8 3.3x3.3, 0.65P**
CASE 511DQ
ISSUE O

DATE 31 OCT 2016




SIDE VIEW




ALL DIMENSIONS AS PER OPTION A UNLESS SPECIFIED

BOTTOM VIEW
(OPTION C)

NOTES:

A. PACKAGE DOES NOT FULLY CONFORM TO JEDEC REGISTRATION MO-240.
B. DIMENSIONS ARE IN MILLIMETERS.
C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN
E. DIMENSIONS DO NOT INCLUDE BURRS OR MOLD FLASH. BURRS OR MOLD FLASH SHALL NOT EXCEED 0.10MM.

| | | | |
|---|---|---|---|
| **DOCUMENT NUMBER:** | **98AON13648G** | Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red. | |
| **DESCRIPTION:** | **WDFN8 3.3X3.3, 0.65P** | | **PAGE 2 OF 2** |

**onsemi** and ONSEMI are trademarks of Semiconductor Components Industries, LLC dba **onsemi** or its subsidiaries in the United States and/or other countries. **onsemi** reserves the right to make changes without further notice to any products herein. **onsemi** makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. **onsemi** does not convey any license under its patent rights nor the rights of others.

© Semiconductor Components Industries, LLC, 2016

**onsemi**, ONSEMI , and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent−Marking.pdf. **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as−is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi** products, including compliance with all laws, regulations and safety requirements or standards, regardless of any support or applications information provided by **onsemi**. "Typical" parameters which may be provided in **onsemi** data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. **onsemi** does not convey any license under any of its intellectual property rights nor the rights of others. **onsemi** products are not designed, intended, or authorized for use as a critical component in life support systems or any FDA Class 3 medical devices or medical devices with a same or similar classification in a foreign jurisdiction or any devices intended for implantation in the human body. Should Buyer purchase or use **onsemi** products for any such unintended or unauthorized application, Buyer shall indemnify and hold **onsemi** and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that **onsemi** was negligent regarding the design or manufacture of the part. **onsemi** is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

## ADDITIONAL INFORMATION

**TECHNICAL PUBLICATIONS**:
**Technical Library:** www.onsemi.com/design/resources/technical−documentation
**onsemi Website:** www.onsemi.com

**ONLINE SUPPORT**: www.onsemi.com/support
**For additional information, please contact your local Sales Representative at**
www.onsemi.com/support/sales